MODIFIED PTO/SB/08 (08-00)
Approved for use through 10/31/2002. OMB 0651-0031
U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE

Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control

ildifficer.							
	Substitute for for					Complet if Known	
	INFORMATION				Application Number	10/608,432	
	STATEMENT BY	Y APPLI	CANT	1 0 3 2000 4	Filing Date	06/30/2003	
			۱. ·	À	First Nam d Inventor	Robert BELLMAN	
			13	76	Group Art Unit	2874	
	(use as many shee	ets as ne	Cescal	M TONOGONE POR	Examiner Name	Unassigned	
Sheet	2	of	3	THAUE	Attorney Docket Number	064951-0204	

	,	NON PATENT LITERATURE DOCUMENTS	
Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.	Τ6
hmh	A16	ARNOLDBIK et al., "Dynamic Behavior of Hydrogen in Silicon Nitride and Oxynitride Films Made by Low- Pressure Chemical Vapor Deposition", The American Physical Society, Physical Review B, Vol. 48, No. 8, Aug. 15, 1993, pp. 5444-5456	
	A17	BOGATYRJOV et al., "Passive Selective Filter for Flattening the Erbium-Doped Fibre Amplifier Gain Spectrum Based on a Feature of the Silicon Oxynitride Fibre Absorption Spectrum", Electronics Letters, Vol. 31, No. 1, Jan. 5, 1995, pp. 61-62	
	A18	BONA et al., "Wavelength Division Multiplexed Add/Drop Ring Technology in Corporate Backbone Networks", Optical Engineering, Vol. 37, No. 12, Dec. 1998, pp. 3218-3228	
	A19	BOSSEBOEUF and BOUCHIER, "Mechanisms of Reactive Ion-Beam Sputtering of Silicon Nitride in Presence of <sup>15</sup> N- or D-Labeled Ammonia," J. Electrochem. Society, Vol. 133, No. 4, April 1986, pp. 810-816	_
	A20	CAVALLARI et al., "Plasma Processing for Silicon Oxynitride Films", J. Electrochem. Soc., Vol. 134, No. 5, May 1987, pp. 1265-1270	
	A21	DENISSE et al., "Annealing of Plasma Silicon Oxynitride Films", J. Appl. Phys., Vol. 60, No. 7, Oct. 1, 1986, pp 2543-2547	
	A22	GERMAN et al., "Silicon-oxynitride Layers for Optical Waveguide Applications," <u>Electrochemical Society</u> <u>Proceedings</u> , Vol. 99-6	
	A23	HABRAKEN et al., "Hydrogen in low-pressure chemical-vapor-deposited silicon (oxy)nitride films," <u>J. Appl. Phys.</u> , January 15, 1986, Vol. 59, No. 2	
	A24	HABRAKEN et al., "Hydrogen in Low-Pressure Chemical-Vapor-Deposited Silicon (Oxy)Nitride Films", J. Appl. Phys. Vol. 59, No. 2, Jan. 15, 1986, pp. 447-453	
	A25	HE et al., "Hydrogen Behavior in PECVD Nitride by SiH, & ND <sub>3</sub> During RTA," Mat. Res. Soc. Symp. Proc., Vol. 424, Apr. 8-12, 1996, San Franciso, CA pp. 109-114	
	A26	HUBNER, "Strong Bragg Gratings Induced with 248 nm Light in Buried Silicon Exynitride Waveguides," XP-000987165	
	A27	OHRING, "The Materials Science of Thin Films", 1992, pp. 181-184	
4	A28	SPEAKMAN et al., "Characterization of PECVD Deposited Silicon Oxynitride Thin Films", Vacuum, Vol. 38, No. 3, 1988, pp. 183-188	

Examiner	$1 \cap 1 \cap 1$	$\alpha$ 1	Data	i
Signature	N-10 ///	1 II	Date	1 2 4//
Oignatur <del>e</del>	Tal 1000	DY Dun	Considered	1 17-1-04
*EVALUATED	1-27-1-27			

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chlef Information Officer, U.S. Patent and Trademark Office, PO Box 1450, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, PO Box 1450,

<sup>\*</sup>EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

¹ Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ³Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.

MODIFIED PTO/SB/08 (08-00) Approved for use through 10/31/2002. OMB 0651-0031

U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control

	Substitute for for		<i>/</i> ^ \	PE		Complete if Known	
	INFORMATION I	DISCLO	SURE	ζ)	Application Number	10/608,432	
ł	STATEMENT BY	Y APPLI			Filing Date	06/30/2003	
i		. 1	י דשם ן	0.5 22.5	First Named Inventor	Robert BELLMAN	
i	(	. *	12	Æ	Group Art Unit	2874	
	(use as many shee	ils as nec	:exxary)		Examiner Name	Unassigned	
Sheet	3	of	3 3	TRADEMAR	Attorney Docket Number	064951-0204	

	NON PATENT LITERATURE DOCUMENTS								
Examiner   Cite   No.1		Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.							
hanh	A29	SPÜHLER et al., "A Very Short Planar Silica Spot-Size Converter Using a Nonperiodic Segmented Waveguide", J. Lightwave Tech., Vol. 16, No. 9, Sept. 1998, pp. 1680-1685							
			-						
·									
	_								
	_	1							

Examiner		1	$\alpha$	D-4-	
Signature	` <i>kI</i>	4/1/2 2	'Al.	Date	1 - 1 - 1
Signature	1720	1000000	140000	Considered	1275-04
*FYAMINED	Initial if reference	appaids and the site			

Initial If reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, PO Box 1450, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, PO Box 1450, Alexandria, Virginia 22313-1450.

¹ Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the Indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 If possible. ⁴Applicant is to place a check mark here if English language Translation is attached.

MODIFIED PTO/SB/08 (08-00)

Approved for use through 10/31/2002. OMB 0651-0031 U.S. Palent and Trademark Office: U.S. DEPARTMENT OF COMMERCE Under the Paperwork Reduction Act of 1995, no persons are required to respond to a collection of information unless it contains a valid OMB control

	ute for form 1449B/PT	<i>-</i>		Complete if Known	
INFORM	ATION DISCLOSE	RE C	Application Number	10/608,432	
STATE	MENT BY APPLICA	∩^~ \ \	Filing Date	06/30/2003	
	· (_	2 (100)	First Named Inventor	Robert BELLMAN	
(upp ====		بر	Group Art Unit	2874	
	any sheets as nec		Examiner Name	Unassigned	
Sheet 1	of 3	PADEMARK	Attorney Docket Number	064951-0204	

	·			U.S. PATENT DOCUMENTS	S	
Examiner	Cite	U.S. Patent	Document		Date of Publication of	Pages, Columns, Lines,
	No.1	Number	Kind Code <sup>2</sup> (if known)	Name of Patentee or Applicant of Cited Document	Cited Document MM-DD-YYYY	Where Relevant Passages or Relevant Figures Appear
hmh	A1	4,962,065		BROWN et al.	10-09-1990	
	A2	5,062,680		IMAMURA et al.	11-05-1991	
	А3	5,264,724	Α	BROWN et al.	1-23-1993	
	A4	5,343,544	A	BOYD et al.	08-30-1994	
	A5	5,694,513	А	OKANIWA	12-02-1997	
	A6	5,979,188	А	OJHA	11-09-1999	
	A7	5,972,765	Α	CLARK et al.	11-26-1999	:
	8A	6,077,791	A	DeTAR	06-20-2000	
	A9	6,229,949	B1	IDO et al.	05-08-2001	
	A10	6,341,190	B1	SUMMERSGILL et al.	01-22-2002	
1/	A11	6,393,185	B1	DEACON	05-21-2002	
V	A12	6,499,318	B1	LEMAIRE et al.	12-31-2002	

	FOREIGN PATENT DOCUMENTS									
Examiner Initials*	Cite No. <sup>1</sup>	Office	oreign Patent [  Number <sup>4</sup>	Nocument Kind Code <sup>5</sup> (if known)	Name of Patentee or Applicant of Cited Documents	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear	T <sup>6</sup>		
hmh	A13	wo	01/64594	A1	INTERNATIONAL BUSINESS MACHINES CORPORATION	09-07-2001				
hmh	A14	JP	09-078244		CANON INC.	03-25-1997				
hmh	A15	EP	0 673 895	A2	AT&T CORP.	09-27-1995				

Examiner	01 00	11	Date	
Signature	Hae Moon	Hyem	Considered	17-3-04
'EXAMINER	Initial if reference conclusion whether an			10 / 01

Burden Hour Statement: This form is estimated to take 2.0 hours to complete. Time will vary depending upon the needs of the individual case. Any comments on the amount of time you are required to complete this form should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, PO Box 1450, Alexandria, Virginia 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Commissioner for Patents, PO Box 1450, Alexandria, Virginia 22313-1450.

lered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>&</sup>lt;sup>1</sup> Unique citation designation number. <sup>2</sup>See attached Kinds of U.S. Patent Documents. <sup>3</sup>Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup>For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup>Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup>Applicant is to place a check mark here if English language Translation is attached.